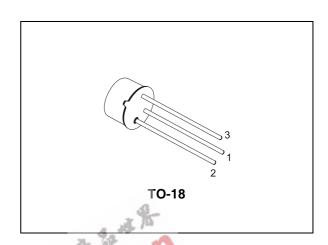


2N3700

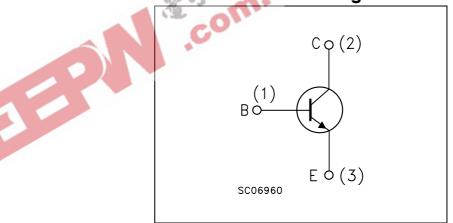
General purpose amplifiers

Description

The 2N3700 is silicon planar epitaxial NPN transistor in Jedec TO-18 metal case. It is intended for small signal, low noise industrial applications.



Internal schematic diagram



Order codes

Part Number	Marking	Package	Packing
2N3700	2N3700	TO-18	Bag

Electrical ratings 2N3700

1 Electrical ratings

Table 1. Absolute maximum rating

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-emitter voltage (I _E = 0)	140	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	80	V
V _{EBO}	Emitter-base voltage (I _C = 0)	7	V
I _C	Collector current	1	Α
	Total dissipation at T _{amb} ≤ 25°C	0.5	W
P_{tot}	at T _{case} ≤ 25°C	1.8	W
	at T _{case} ≤ 100°C	1	W
T _{stg}	Storage temperature	-65 to 200	°C
T _J	Max. operating junction temperature	200	°C

Table 2. Thermal data

Symbol	Parameter	3.3 %	Value	Unit
R _{thj-case}	Thermal resistance junction-case	max	97	°C/W
R _{thj-amb}	Thermal resistance junction-ambient	max	350	°C/W
		.60		

2N3700 Electrical characteristics

2 Electrical characteristics

 $(T_{CASE} = 25^{\circ}C; unless otherwise specified)$

Table 3. Electrical characteristics

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (I _E = 0)	V _{CB} = 90V V _{CB} = 90V	T _{amb} = 150°C			10 10	nA μA
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = 5V				10	nA
V _{(BR)CBO}	Collector-base breakdown voltage (I _E = 0)	I _C = 100μA		140			V
V _{(BR)CEO} ⁽¹⁾	Collector-emitter breakdown voltage (I _B = 0)	I _C = 30mA		80			V
V _{(BR)EBO}	Emitter-base breakdown voltage $(I_C = 0)$	I _E = 100μA		7			V
,, (1)	Collector-emitter saturation	I _C = 150mA	I _B = 15mA	3 %		0.2	V
V _{CE(sat)} (1)	voltage	$I_{C} = 0.5A$	$I_B = 50 \text{mA}$			0.5	٧
V _{BE(sat)} (1)	Base-emitter saturation voltage	I _C = 150mA	I _B = 15mA	C		1.1	٧
h _{FE}	DC current gain	$I_{C} = 0.1 \text{mA}$ $I_{C} = 10 \text{mA}$ $I_{C} = 150 \text{mA}$ $I_{C} = 500 \text{mA}$ $I_{C} = 1 \text{A}$ $I_{C} = 150 \text{mA}$ $T_{amb} = -55 ^{\circ}\text{C}$	$V_{CE} = 10V$	50 90 100 50 15		300	
h _{fe}	Small signal current gain	I _C = 1mA f = 1kHz	$V_{CE} = 5V$	80		400	
f _T	Transition frequency	I _C = 50mA f = 20MHz	V _{CE} = 10V		100		MHz
C _{EBO}	Emitter-base capacitance	I _C = 0 f = 1MHz	V _{EB} = 0.5V		60		pF
C _{CBO}	Collector-base capacitance	I _E = 0 f = 1MHz	V _{CB} = 10V		12		pF
r _{bb'} C _{b'c}	Feedback time constant	I _C = 10mA f = 4MHz	V _{CB} = 10V	25		400	ps

Note: (1) Pulsed: Pulse duration = 300 μ s, duty cycle \leq 1 %

Package mechanical data 2N3700

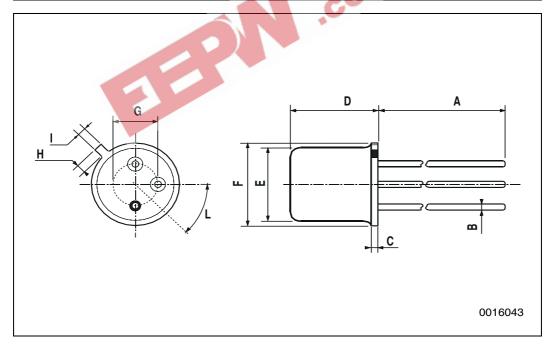
3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com



TO-18 MECHANICAL DATA

DIM.	mm			inch		
2	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α		12.7			0.500	
В			0.49			0.019
D			5.3			0.208
E			4.9			0.193
F			5.8			0.228
G	2.54			0.100	a	
н			1.2	4.1	E Th	0.047
ı			1.16	4. 75.3	CI	0.045
L	45°		3	45°		



Revision history 2N3700

4 Revision history

Table 4. Revision history

Date	Revision	Changes	
31-Jan-1989	1	First release	
06-Nov-2006	2	The document has been reformatted	



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